2SD1006

GENERAL PURPOSE TRANSISTOR
NPN SILICONEPITAXIAL TRANSISTORS

DESCRIPTION

The 2SD1006 is available in SOT89-3 package

- High collector to emitter voltage: V_{CEO}>100V
- Audio Frequency Power Amplifier Application
- Complement to PNP type 2SB805

ORDERING INFORMATION

Package Type	Part Number	
	2SD1006-HM	
SOT89-3	2SD1006-HL	
	2SD1006-HK	
Note	SPQ: 1,000pcs/Reel	
AiT provides all RoHS Compliant Products		

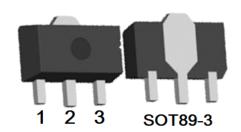
h_{FE} Classification

h _{FE}	НМ	HL	HK
Range	90~180	135~270	200~400

MACHANICAL DATA

Case: SOT89-3

PIN DESCRIPTION



PIN	PIN DESCRIPTION	
1	BASE	
2	COLLECTOR	
3	EMITTER	

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ABSOLUTE MAXIMUM RATINGS

T_A=25°C, unless otherwise specified

Parameter	Symbol	Value	Units
Collector-Base Voltage	V _{CBO}	100	V
Collector-Emitter Voltage	Vceo	100	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current	Ic	0.7	Α
Collector Current(pulse)*	I _{C(pu)}	1.2	Α
Collector I Power Dissipation**	Pc	2	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55~+150	°C

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

T_A=25°C, unless otherwise specified

Parameter	Symbol	Min.	Тур.	Max.	Unit
Base- emitter voltage ¹	V _{BE}	550	620	650	mV
Collector cutoff current	Ісво	1	1	100	nA
Emitter cutoff current	I _{EBO}	1	1	100	nA
DC aumont main1	L *	45	200	-	-
DC current gain ¹	h _{FE} *	90	200	400	-
Collector-emitter saturation voltage ¹	V _{CE} (sat)	1	0.3	0.6	V
Base-emitter saturation voltage*	V _{BE} (sat)	-	0.9	1.5	٧
Transition frequency	f⊤	-	10	-	рF
output capacitance	Cob	-	90	-	MHz

*hFE Classification

Part Number	2SD1006-HM	2SD1006-HL	2SD1006-HK
h _{FE}	90~180	135~270	200~400

^{*}PW≦350µs, duty cycle≦2%

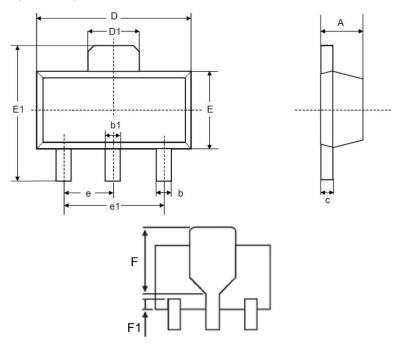
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^{*}PW≦10ms,duty cycle≦50%

^{**}When mounted on ceramic substrate of 16cm² x 0.7mm

PACKAGE INFORMATION

Dimension in SOT89-3 (Unit: mm)



Symbol	Min.	Max.
Α	1.400	1.600
b	0.380	0.580
b1	0.430	0.630
С	0.340	0.540
D	4.400	4.600
D1	1.700	1.900
E	2.400	2.600
E1	3.900	4.100
F	2.500	2.700
F1	0.300	0.500
е	1.400	1.600
e1	2.900	3.100
L	0.900	1.200

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